


<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  		ATTY. DOCKET NO. <b>050212-0716</b>		SERIAL NO. <b>10/580,346</b>		
(PTO-1449)		APPLICANT <b>Akihiko NAMBA, et al.</b>				
FILING DATE <b>May 25, 2006</b>		GROUP <b>4146</b> <b>Not Yet Assigned</b>				
<b>U.S. PATENT DOCUMENTS</b>						
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code2 (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
		US				
		US				
		US				
		US				
		US				
		US				
		US				
<b>FOREIGN PATENT DOCUMENTS</b>						
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number + -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes      No
/R.H./		JP 62-70295 A	03-31-1987	SUMITOMO ELECTRIC IND LTD		JAPAN (w/English Abstract)
/R.H./		JP 63-302516 A	12-09-1988	SUMITOMO ELECTRIC IND LTD		JAPAN (w/English Abstract)
/R.H./		JP 7-69794	03-13-1995	SUMITOMO ELECTRIC IND LTD	Corresponds to JP 3374866 B2	ABSTRACT ONLY
/R.H./		JP 3374866 B2	11-29-2002		Corresponds to JP 7-69794	X
<b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>						
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				
/R.H./		H. SHIOMI ET AL., "Characterization of Boron-Doped Diamond Epitaxial Films," Japanese Journal of Applied Physics, Vol. 30, No. 7, July 1991, pp. 1363-1366				
/R.H./		"Ohmic Electrode of Phosphorus Doped N-Type Diamond," NEW DIAMOND, vol. 17, No. 1 (2001), pg. 6-12				
/R.H./		S KOIZUMI ET AL., "Growth and characterization of phosphorous doped {111} homoepitaxial diamond thin films," Appl. Phys. Lett., Vol. 71, No. 8, August 1997, American Institute of Physics, p. 1065-1067				
/R.H./		M. G. NISHITANI ET AL., "Synthesis of S-doped N-Type Diamond Semiconductor," NEW DIAMOND, Vol. 15, No. 4 (1999), p. 20-22				
/R.H./		International Preliminary Report on Patentability issued in corresponding International Application No. PCT/JP2004 /017077, mailed August 3, 2006, and the Written Opinion of the International Searching Authority				
/Robert Hubel/ EXAMINER			02/06/2006 DATE CONSIDERED			

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.